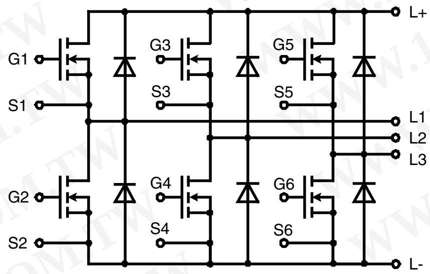
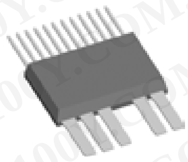
Three phase full Bridge

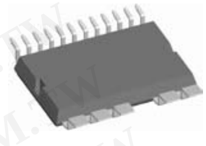
with Trench MOSFETs
in DCB isolated high current package

V_{DSS} = 100 V
I_{D25} = 90 A
$R_{DSon\ typ.}$ = 7.5 mΩ





Straight leads



Surface Mount Device

MOSFETs

Symbol	Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	100	V
V_{GS}		± 20	V
I_{D25} I_{D90}	T_C = 25°C T_C = 90°C	90 68	A A
I_{F25} I_{F90}	T_C = 25°C (diode) T_C = 90°C (diode)	90 68	A A

Symbol	Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
R_{DSon} 1)	on chip level at V_{GS} = 10 V; I_D = 80 A	T_J = 25°C T_J = 125°C		7.5 14	8.5	mΩ mΩ
$V_{GS(th)}$	V_{DS} = 20 V; I_D = 250 µA		2.5		4.5	V
I_{DSS}	V_{DS} = V_{DSS}; V_{GS} = 0 V	T_J = 25°C T_J = 125°C		 0.1	1	µA mA
I_{GSS}	V_{GS} = ± 20 V; V_{DS} = 0 V				0.2	µA
Q_g Q_{gs} Q_{gd}	V_{GS} = 10 V; V_{DS} = 65 V; I_D = 90 A			90 30 30		nC nC nC
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off} E_{recoff}	inductive load V_{GS} = 10 V; V_{DS} = 48 V I_D = 70 A; R_G = 33 Ω; T_J = 125°C			130 95 290 55 0.4 0.4 0.007		ns ns ns ns mJ mJ mJ
R_{thJC} R_{thJH}	 with heat transfer paste (IXYS test setup)			 1.3	1.0 1.6	K/W K/W

1) $V_{DS} = I_D \cdot (R_{DS(on)} + 2R_{Pin\ to\ Chip})$

Applications

AC drives
- in automobiles
  - electric power steering
  - starter generator
- in industrial vehicles
  - propulsion drives
  - fork lift drives
- in battery supplied equipment

Features

- MOSFETs in trench technology:
  - low R_{DSon}
  - optimized intrinsic reverse diode
- package:
  - high level of integration
  - high current capability 300 A max.
  - aux. terminals for MOSFET control
  - terminals for soldering or welding connections
  - isolated DCB ceramic base plate with optimized heat transfer
- Space and weight savings

Package options

- 2 lead frames available
  - straight leads (SL)
  - SMD lead version (SMD)

IXYS reserves the right to change limits, test conditions and dimensions.

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Source-Drain Diode

Symbol	Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
V_{SD}	(diode) I_F = 70 A; V_{GS} = 0 V		0.9	1.2	V
t_{rr}	I_F = 70 A; $-di_F/dt$ = 800 A/µs; V_R = 48 V		55		ns
Q_{RM}			0.95		µC
I_{RM}			33		A

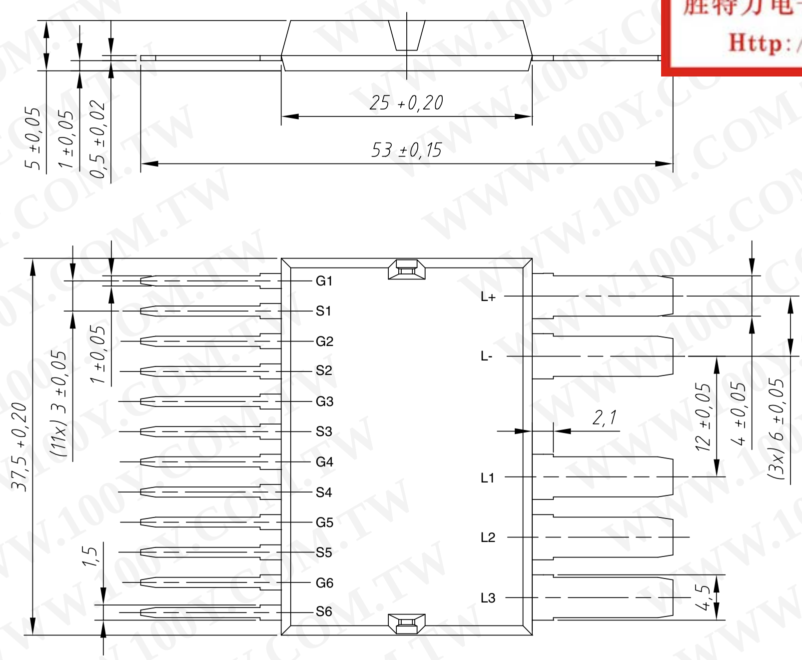
Component

Symbol	Conditions	Maximum Ratings	
I_{RMS}	per pin in main current paths (P+, N-, L1, L2, L3) may be additionally limited by external connections	300	A
T_J		-55...+175	°C
T_{stg}		-55...+125	°C
V_{ISOL}	$I_{ISOL} \leq$ 1 mA, 50/60 Hz, f = 1 minute	1000	V~
F_C	mounting force with clip	50 - 250	N

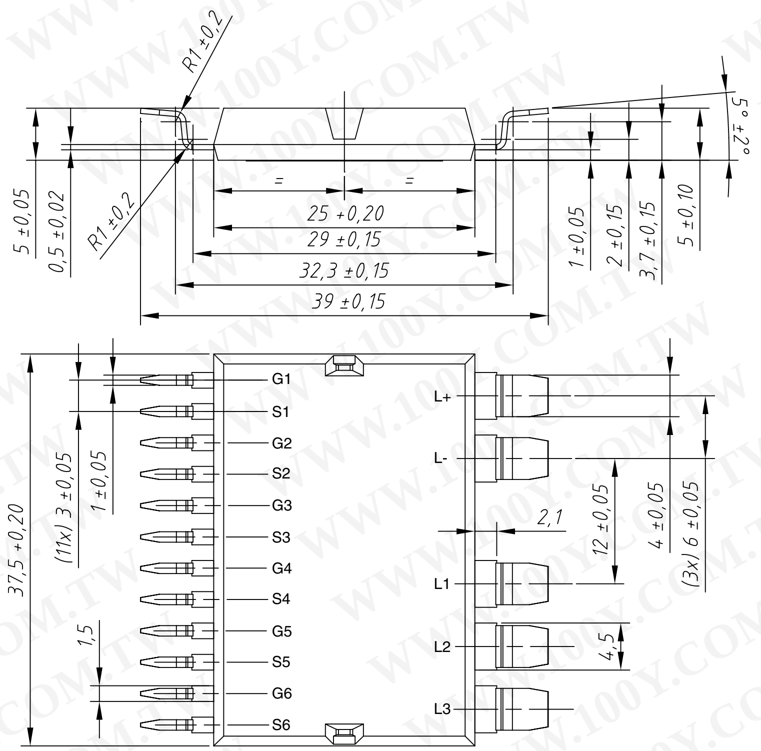
Symbol	Conditions	Characteristic Values min.	typ.	max.	
$R_{pin\ to\ chip}$ [1]			0.6		mΩ
C_P	coupling capacity between shorted pins and mounting tab in the case		160		pF
Weight			25		g

[1] $V_{DS} = I_D \cdot (R_{DS(on)} + 2R_{Pin\ to\ Chip})$

Straight **L**eads GWM 100-01X1-SL



Surface **M**ount **D**evice GWM 100-01X1-SMD



Leads	Ordering	Part Name & Packing Unit Marking	Part Marking	Delivering Mode	Base Qty.	Ordering Code
Straight	Standard	GWM 100-01X1 - SL	GWM 100-01X1	Blister	36	505 535
SMD	Standard	GWM 100-01X1 - SMD	GWM 100-01X1	Blister	36	505 542

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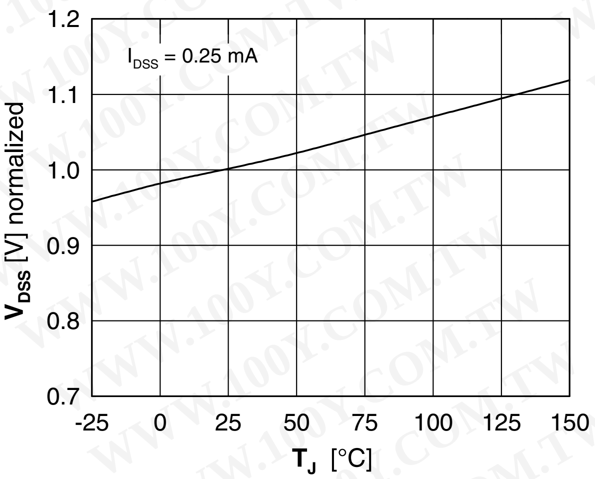

Fig. 1 Drain source breakdown voltage V_{DSS} vs. junction temperature T_J

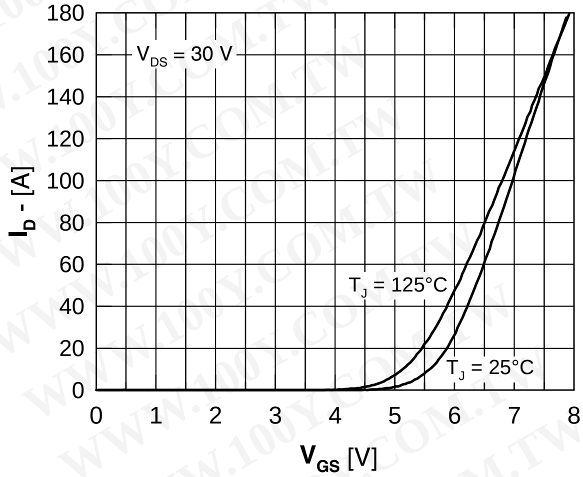

Fig. 2 Typical transfer characteristic

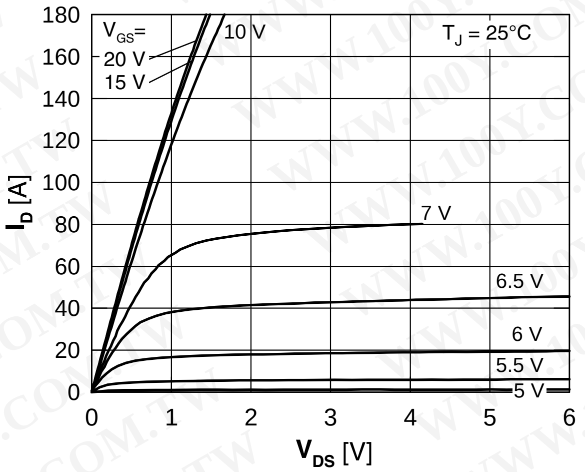

Fig. 3 Typical output characteristic

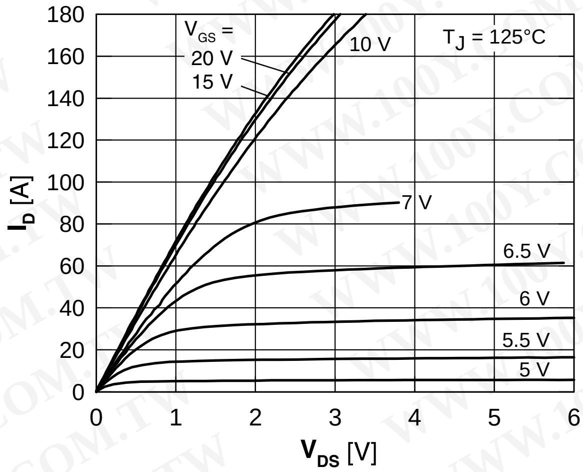

Fig. 4 Typical output characteristic

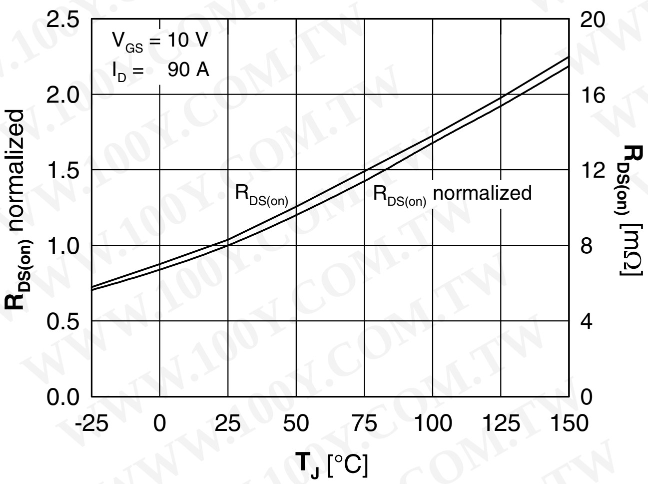

Fig. 5 Drain source on-state resistance $R_{DS(on)}$ versus junction temperature T_J

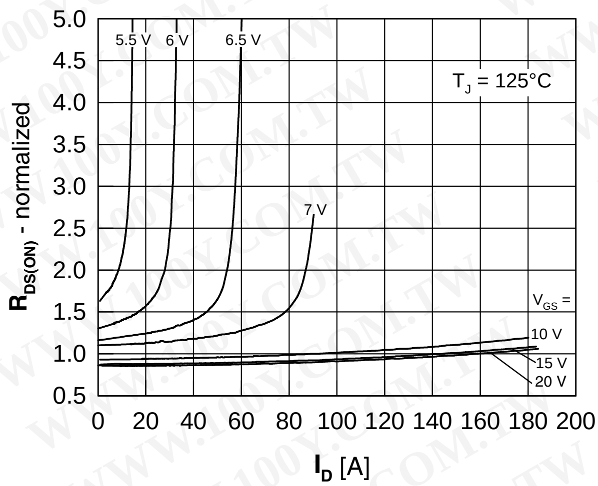

Fig. 6 Drain source on-state resistance $R_{DS(on)}$ versus I_D

IXYS reserves the right to change limits, test conditions and dimensions.

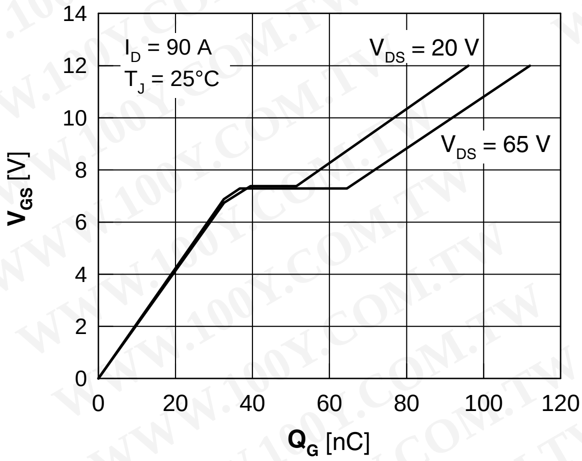

Fig.7 Gate charge characteristic

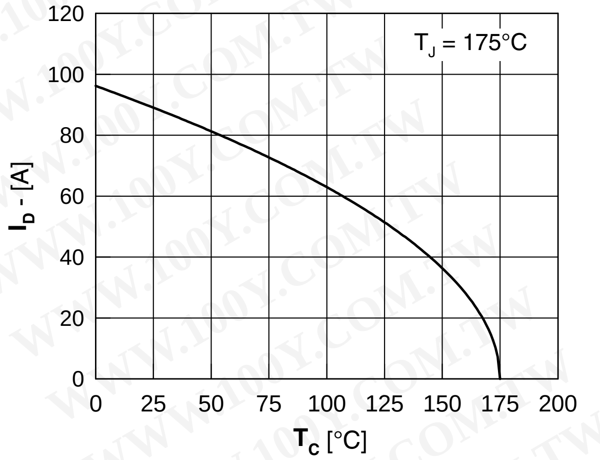

Fig. 8 Drain current I_D vs. case temperature T_C

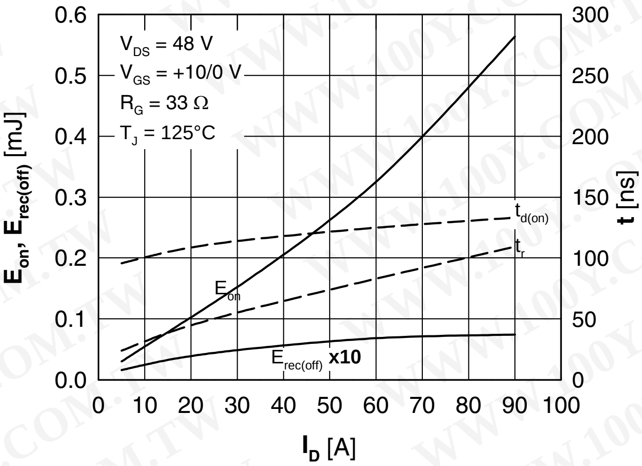

Fig. 9 Typ. turn-on energy & switching times vs. collector current, inductive switching

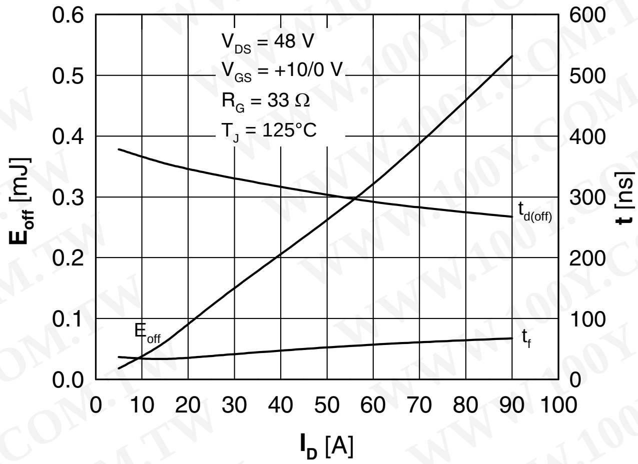

Fig. 10 Typ. turn-off energy & switching times vs. collector current, inductive switching

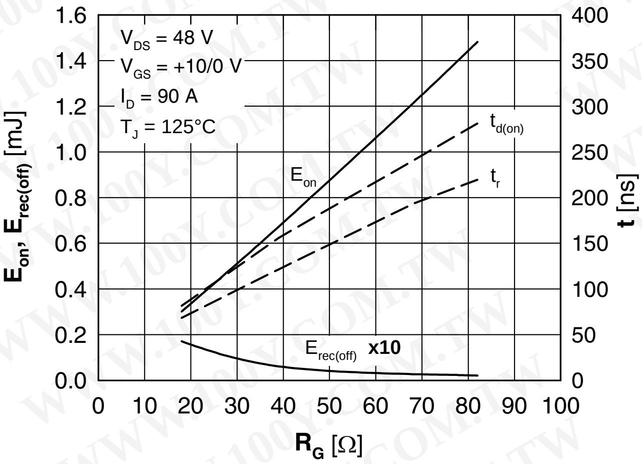

Fig. 11 Typ. turn-on energy & switching times vs. gate resistor, inductive switching

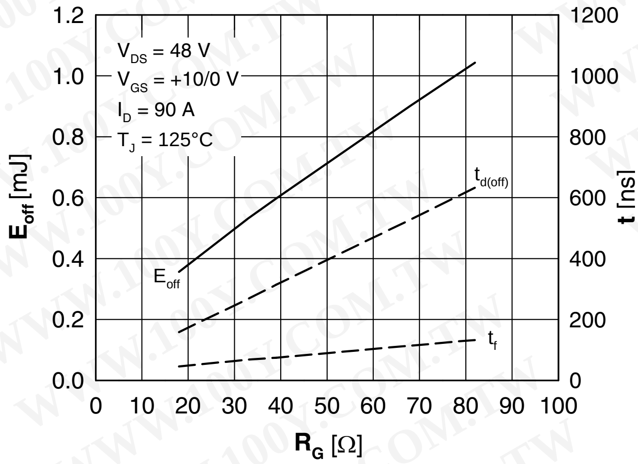

Fig. 12 Typ. turn-off energy & switching times vs. gate resistor, inductive switching

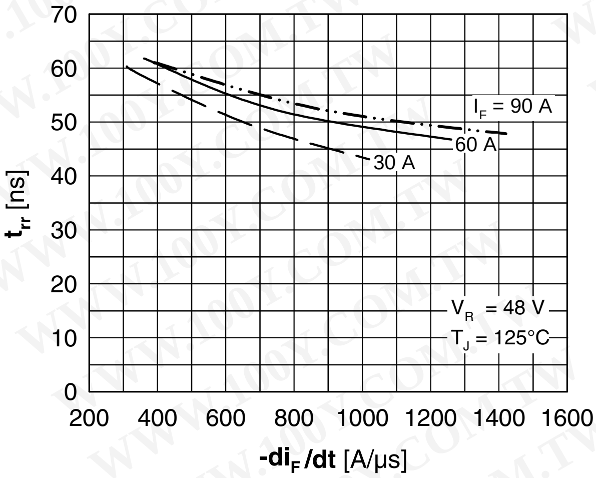

Fig. 13 Reverse recovery time t_{rr} of the body diode vs. di/dt

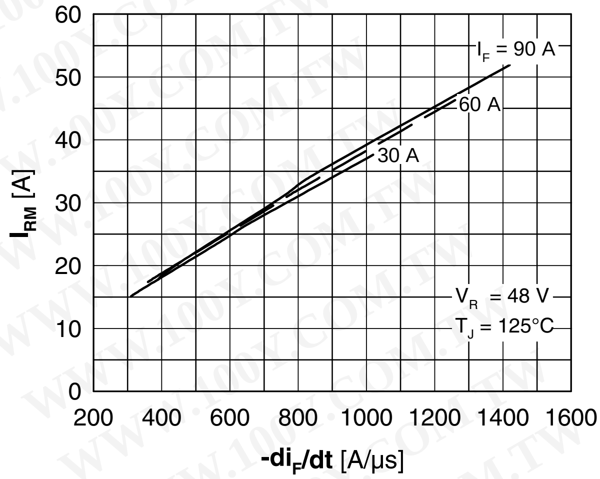

Fig. 14 Reverse recovery current I_{RM} of the body diode vs. di/dt

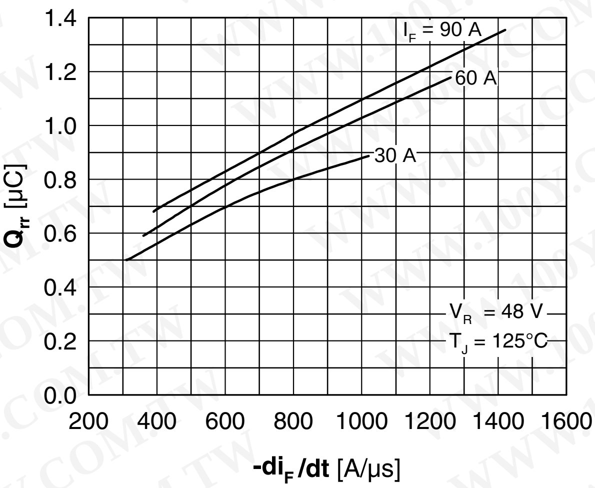

Fig. 15 Reverse recovery charge Q_{rr} of the body diode vs. di/dt

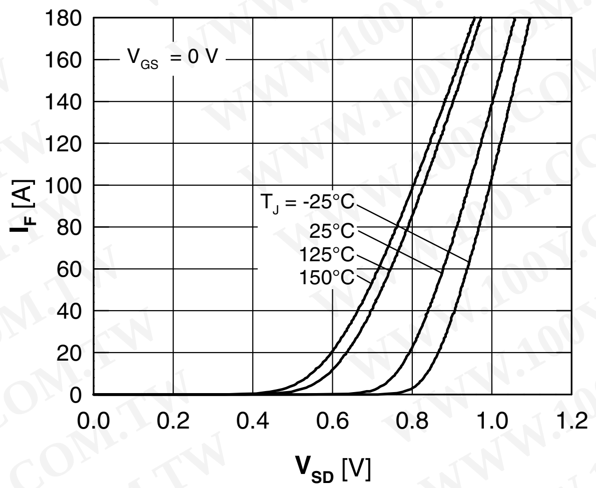

Fig. 16 Source drain diode current I_F vs. source drain voltage V_{SD} (body diode)

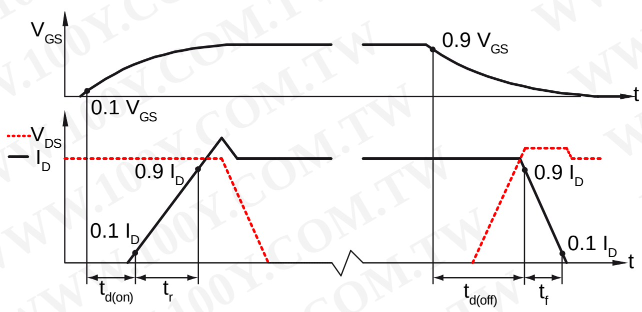

Fig. 17 Definition of switching times

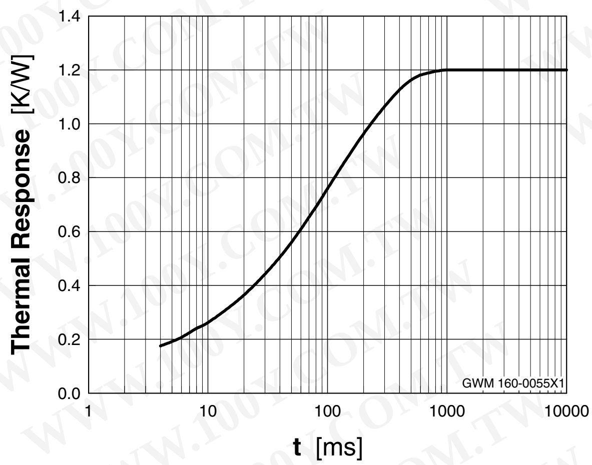

Fig. 18 Typ. thermal impedance junction to heatsink Z_{thJH} with heat transfer paste